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U.S.S.N. 10/051,241

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SPECIFICATION AMENDMENTS

[0027] Similar substrates comprising platinum and silicon oxide layers were polished with seven different chemical mechanical polishing systems, each of which comprised the same polishing pad in conjunction with a different polishing composition (Polishing Compositions 1A-1G). Polishing Composition 1A (control) comprised 8 wt.% alumina abrasive and 1 wt.% hydrogen peroxide with no amine-containing polymer. Polishing Compositions 1B-1G were the same except that they further comprised an amine-containing polymer. Polishing Composition 1B and 1C (comparative) comprised 1 wt.% of polyethylenimine (MW = 20,000) and polyethylenimine (MW = 80,000), respectively. Polishing Composition 1D (invention) comprised 1 wt.% poly(diallyldimethylammonium chloride). Polishing Compositions 1E, 1F, and 1G (invention) comprised 1 wt.% polyaminoamide (MW = 10,000), 0.1 wt.% polyaminoamide (MW = 10,000), and 1 wt.% polyaminoamide (MW = 80,000), respectively. The removal rates for the platinum and silicon oxide layer of the substrates were measured for each of the chemical-mechanical polishing systems. The removal rates (RR) and selectivities are recited in the following Table:

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